PCN Number:			2022101	2000.2A PCN Date:						October 19, 2022
Titl	e:	-		ditior	nal Fab Site (RFAB)	and Ass	embl	ly/Te	est Site	e (MLA) options for
		select de	evices							
Customer Contact:			PCN	<u>Manager</u>		Dep	ot:		Quality Services	
Proposed 1 st Ship Date:			Apr	12, 2023	Sample accept				Nov 12, 2022*	
*Sa	mple r	equests	received	a fte	r November 12, 2	. <mark>022 wi</mark> l	l no	t be	suppo	orted.
Change Type:										
\boxtimes	Assem	bly Site		Assembly Process			\boxtimes	Asser	nbly Materials	
Design			Electrical Specification					Mech	anical Specification	
🛛 Test Site			Packing/Shipping/Labeling					Test I	Process	
Wafer Bump Site			Wafer Bump Material					Wafe	Bump Process	
🛛 Wafer Fab Site			Wafer Fab Materials					Wafe	- Fab Process	
				Part number change						
	DCN Detaile									

PCN Details

Description of Change:

Revision A is to update the Assembly Construction differences table in the Description of change section. The corrections are noted below and are in **bold yellow highlight.**

Texas Instruments is pleased to announce the qualification of RFAB as an additional wafer fab site and MLA as additional assembly/test site options for the devices listed in the "Product Affected" section.

C	urrent Fab Site	9	Additional Fab Site				
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter		
MIHO	LBC8	200 mm	RFAB	LBC8	300 mm		

Assembly construction differences/BOM options are as follows:

	TAI Current	New (TAI + MLA)
Bond wire diameter composition, diameter	Au, 0.8 0.96 mil	0.8

Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
🛛 No Change	🛛 No Change	🛛 No Change	🛛 No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
MIHO8	MH8	JPN	Iba ra ki
RFAB	RFB	USA	Richa rdso n

Assembly/Test Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City	
TAI	TAI	TWN	Chung Ho, New Taipei City	
MLA	MLA		Kuala Lumpur	

Sample product shipping label (not actual product label)

.....

UCC21739QDWQ1

TEXAS INSTRUMENTS MADE IN: Malaysia 20C: 20: MSL 2 /260C/1 YEAR SEAL MSL 1 /235C/UNLIM 03/29 OPT: ITEM: 39 LBL: 5A (L)TO:175	оч рт /04	1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 31T)LOT: 3959047MLA 4W) TKY (1T) 75234835 P) 2P) REV: (V) 003331 201) CSO: SHE (21L) CCO: US 22L) ASO: MLA (23L) ACO: MY	12			
Product Affected:						
UCC21710QDWQ1	UCC21732QDWRQ1	UCC21739QDWRQ1	UCC21755QDWRQ1			
UCC21710QDWRQ1	UCC21737QDWRQ1	UCC21750QDWQ1 UCC21759QDWQ1				

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

Approve Date 08-SEPTEMBER-2022

UCC21750QDWRQ1

Product Attributes

Attributes	Qual Device:	Qual Device:	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:
Attributes	UCC21732QDWQ1	UCC21737QDWQ1	UCC21750QDWQ1	UCC21737QDWQ1	UCC23513QDWYQ1	ISO6741QDWQ1
Automotive Grade Level	Grade 1	Grade 1				
Operating Temp Range (C)	-40 to 125	-40 to 125				
Product Function	Power Management	Interface				
Wafer Fab Supplier	RFAB, RFAB	MH8, MH8				
Assembly Site	MLA	MLA	MLA	TAI	TAI	MLA
Package Group	SOIC	SOIC	SOIC	SOIC	SOIC	SOIC
Package Designator	DW	DW	DW	DW	DWY	DW
Pin Count	16	16	16	16	6	16

QBS: Qual By Similarity

UCC21732QDWQ1

Qual Device UCC21732QDWQ1 is qualified at MSL3 260C
Qual Device UCC21737QDWQ1 is qualified at MSL3 260C

Qual Device UCC21737QDWQ1 is qualified at MSL3 200C
Qual Device UCC21750QDWQ1 is qualified at MSL3 260C

UCC21759QDWRQ1

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC21732QDWQ1	Qual Device: UCC21737QDWQ1	Qual Device:	QBS Reference: 1 UCC21737QDWQ	QBS Reference: 1 UCC23513QDWYO	QBS Referenc
Test Group	est Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J- STD-020	3	77	Preconditioning	MSL2 260C	1 Step	-	-	-	-	No Fails	No Fails
		JESD22- A113											
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL3 260C	1 Step		No Fails		No Fails	-	
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours		1/77/0	-	1/77/0	3/231/0	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	1/77/0		1/77/0	3/231/0	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	1/77/0		1/77/0	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	1/5/0		1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours		1/77/0		1/77/0		3/135/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours				-	3/135/0	-
Test Group	B - Acce	lerated Lifetim	e Simula	tion Tes	ts								
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours		1/77/0		1/77/0	3/231/0	3/231/0
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours				-	3/2400/0	-
Test Group	C - Pack	age Assembly	Integrity	Tests									
WBS	C 1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0
SD	СЗ	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-			-	-	1/15/0	1/15/0
SD	СЗ	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	•	-	-	1/15/0	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	1/10/0	1/10/0	1/10/0	3/30/0	3/30/0

Test Group	D - Die F	abrication Relia	ability Te	sts									
EM	D1	JESD61	-	-	Electromigration		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	•	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	•	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-		Negative Bias Temperature Instability		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verificatio	n Tests										
ESD	E2	AEC Q100- 002	1	3	ESD HBM		2000 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	•	500 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	Qual Device	Qual Device	QBS Reference	QBS Reference	QBS Reference

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

 The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

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